



FCP104N60

N-Channel SuperFET® II MOSFET

600 V, 37 A, 104 mΩ

Features

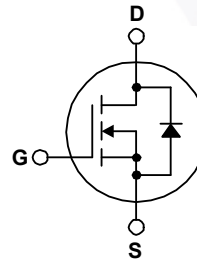
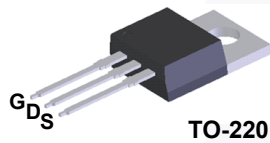
- 650 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 96\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 63\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 280\text{ pF}$)
- 100% Avalanche Tested
- RoHS Compliant

Applications

- Telecom / Server Power Supplies
- Industrial Power Supplies

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is suitable for various AC/DC power conversion for system miniaturization and higher efficiency.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCP104N60	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate to Source Voltage	- DC	± 20
		- AC ($f > 1\text{ Hz}$)	± 30
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	37
		- Continuous ($T_C = 100^\circ\text{C}$)	24
I_{DM}	Drain Current	- Pulsed (Note 1)	111
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	809
I_{AR}	Avalanche Current	(Note 1)	6.8
E_{AR}	Repetitive Avalanche Energy	(Note 1)	3.57
dv/dt	MOSFET dv/dt		100
	Peak Diode Recovery dv/dt	(Note 3)	20
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	357
		- Derate Above 25°C	2.85
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FCP104N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.35	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP104N60	FCP104N60	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 25^\circ\text{C}$	600	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 150^\circ\text{C}$	650	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C	-	0.67	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_C = 125^\circ\text{C}$	-	1.98	-	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.5	-	3.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 18.5\text{ A}$	-	96	104	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 18.5\text{ A}$	-	33	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	3130	4165	pF
C_{oss}	Output Capacitance		-	75	100	pF
C_{rSS}	Reverse Transfer Capacitance		-	3.66	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$	-	280	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}, I_D = 18.5\text{ A}, V_{GS} = 10\text{ V}$	-	63	82	nC
Q_{gs}	Gate to Source Gate Charge		-	14	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	15	-
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	0.97	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 18.5\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.7\text{ }\Omega$	-	26	62	ns
t_r	Turn-On Rise Time		-	18	46	ns
$t_{d(off)}$	Turn-Off Delay Time		-	72	154	ns
t_f	Turn-Off Fall Time		(Note 4)	-	3.3	17

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	37	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	114	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 18.5\text{ A}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_{SD} = 18.5\text{ A}$	-	414	-	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100\text{ A}/\mu\text{s}$	-	8.8	-	μC

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. $I_{AS} = 6.8\text{ A}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 18.5\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq 380\text{ V}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

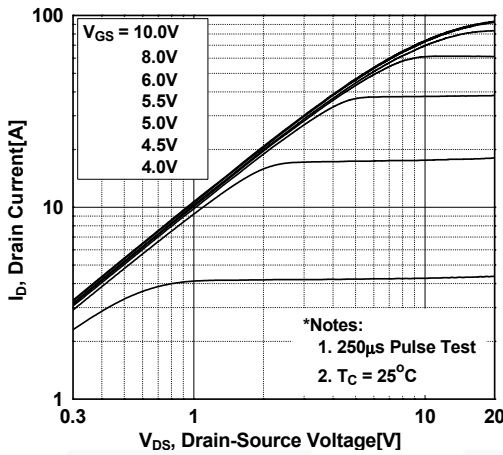


Figure 2. Transfer Characteristics

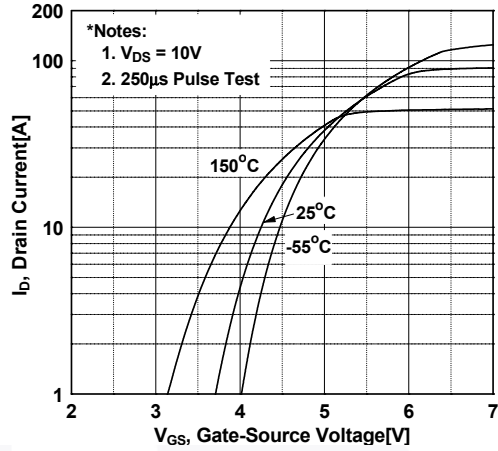


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

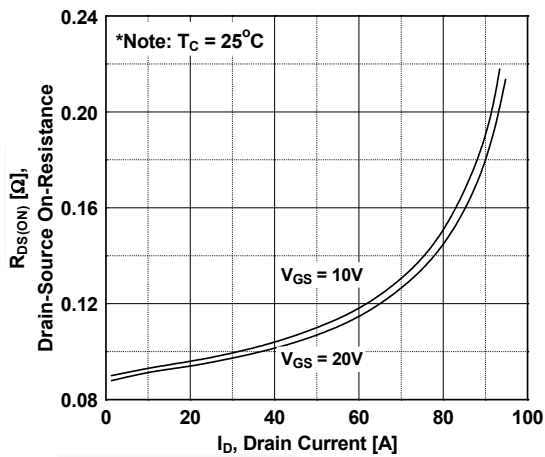


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

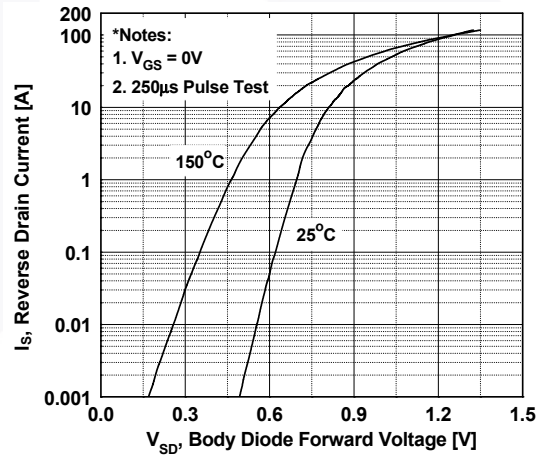


Figure 5. Capacitance Characteristics

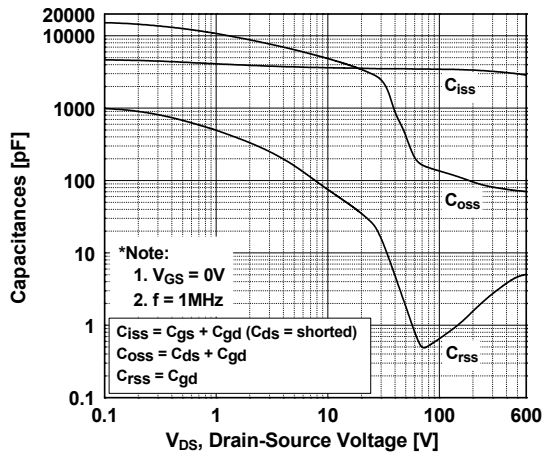
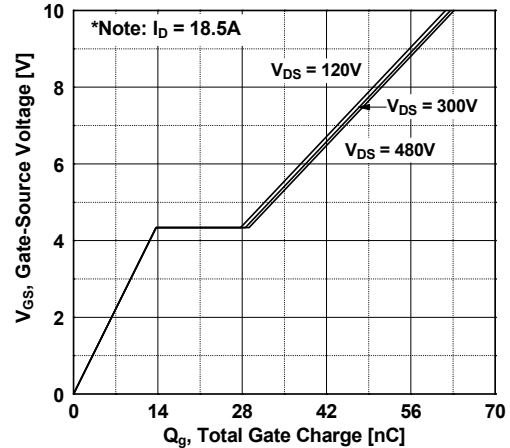


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

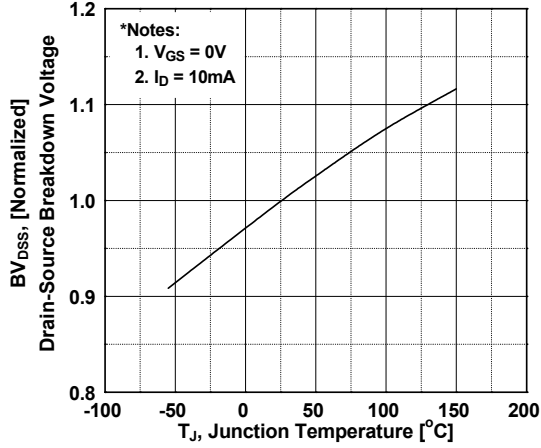


Figure 8. On-Resistance Variation vs. Temperature

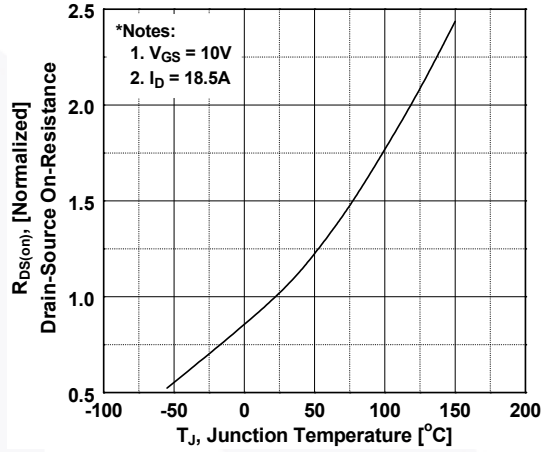


Figure 9. Maximum Safe Operating Area

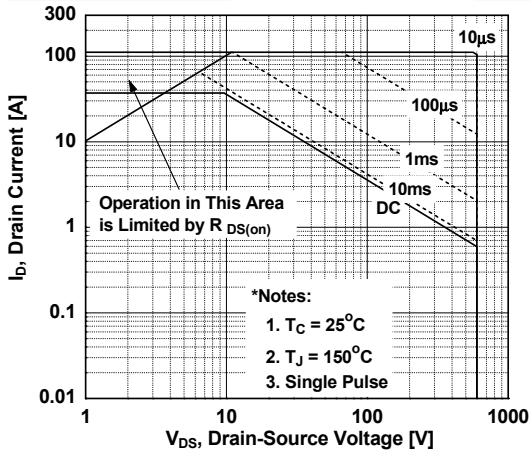


Figure 10. Maximum Drain Current vs. Case Temperature

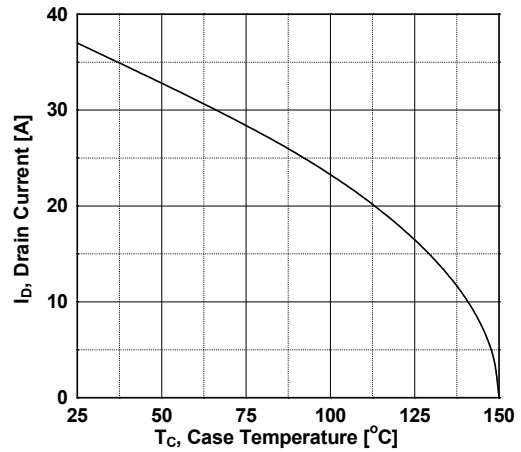
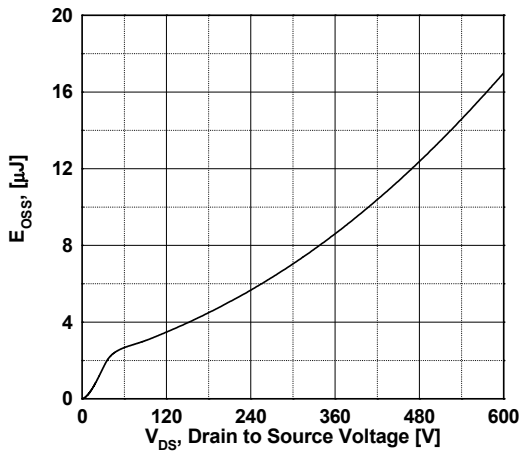


Figure 11. Eoss vs. Drain to Source Voltage



Typical Characteristics (Continued)

Figure 12. Transient Thermal Response Curve

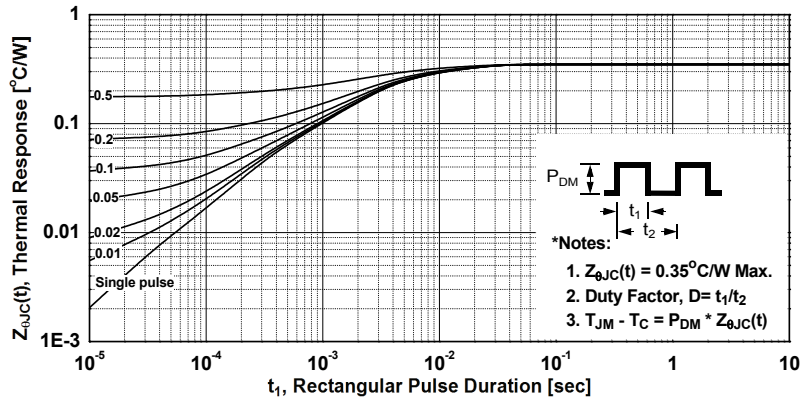


Figure 13. Gate Charge Test Circuit & Waveform

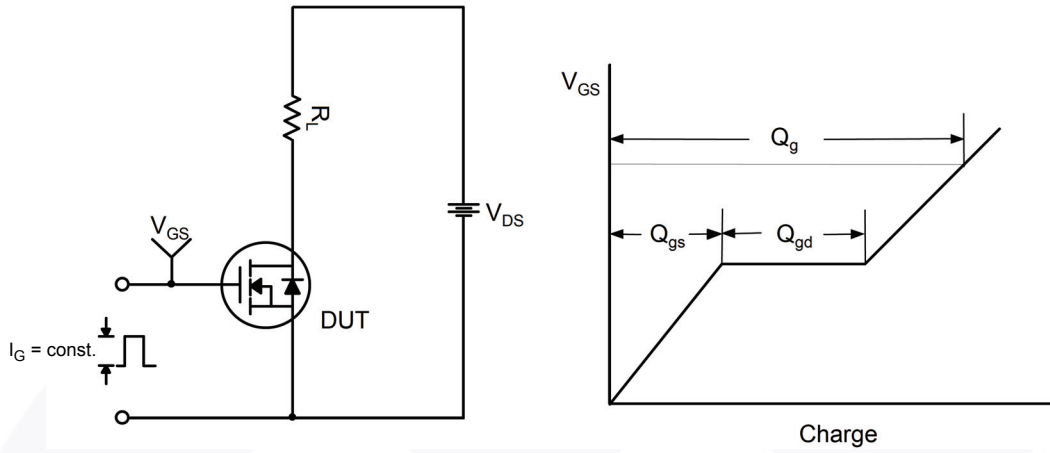


Figure 14. Resistive Switching Test Circuit & Waveforms

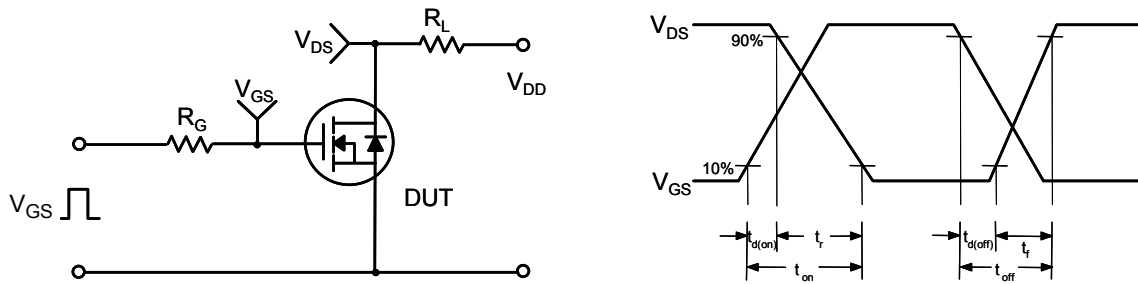


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

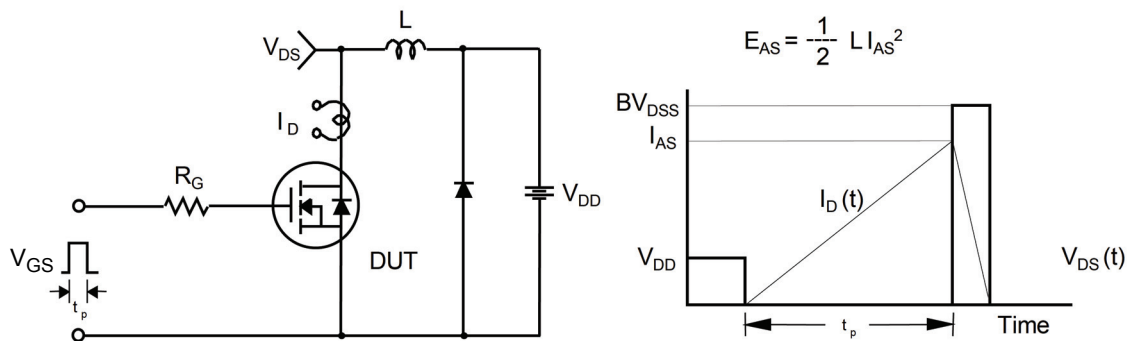
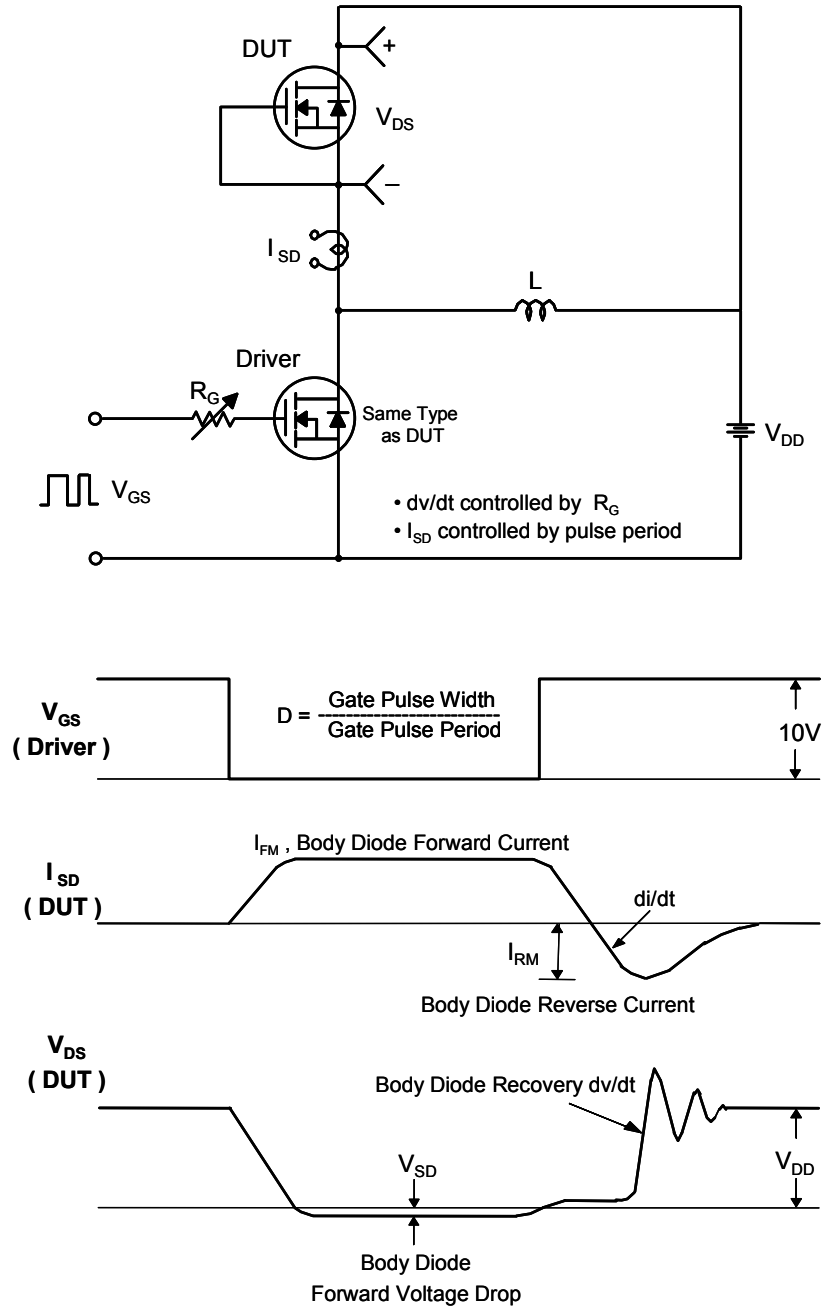
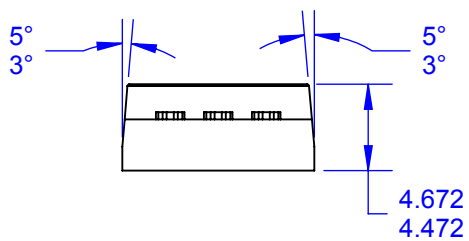
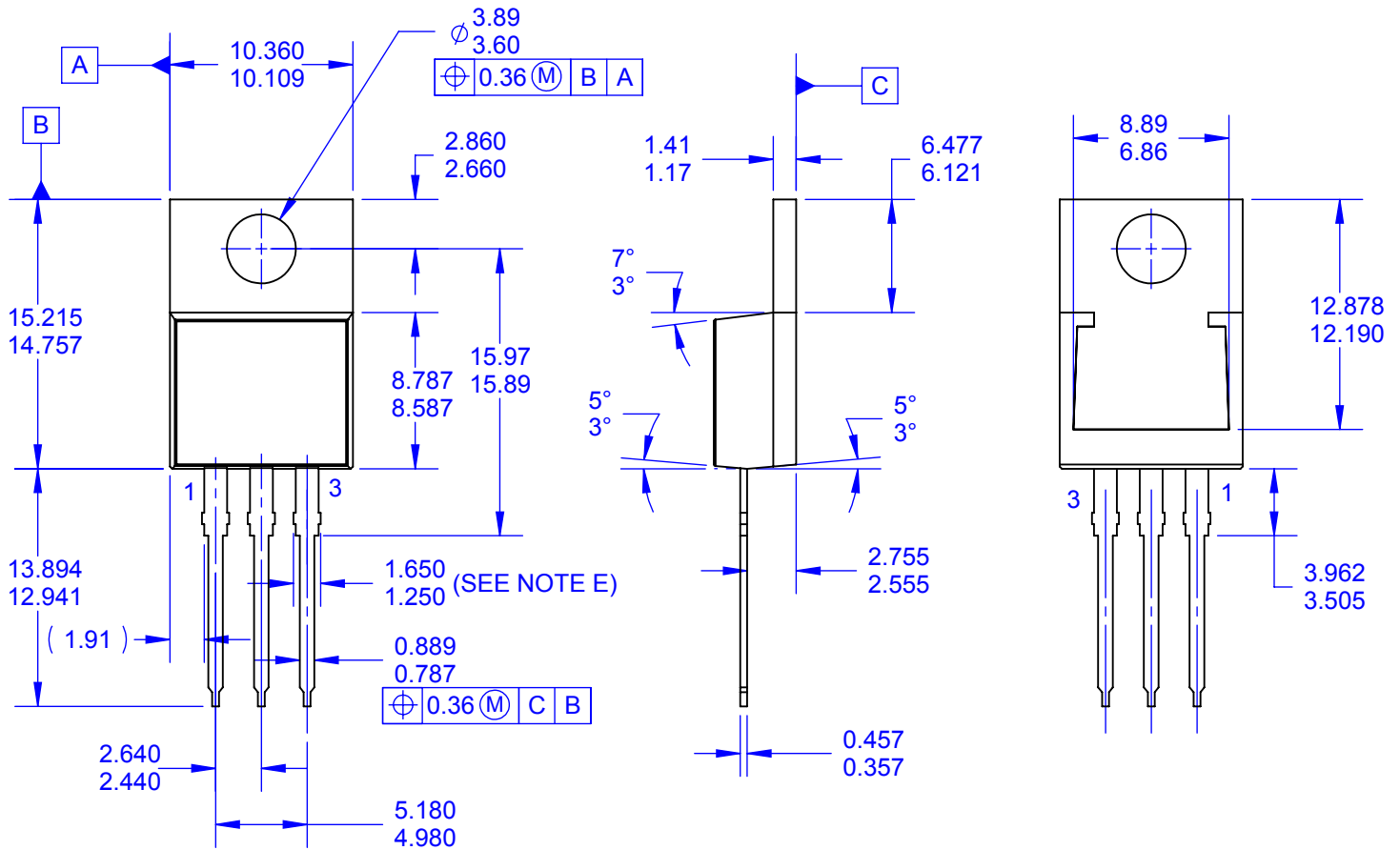


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms





NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220 VARIATION AB
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. MAX WIDTH FOR F102 DEVICE = 1.35mm.
- F. DRAWING FILE NAME: TO220T03REV4.
- G. FAIRCHILD SEMICONDUCTOR.

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